imall

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CONFIGURABLE MULTIPLE-FUNCTION GATE

Description

The 74LVC1G97 is a single 3-input positive configurable multiple function gate with a standard push-pull output. The output state is determined by eight patterns of 3-bit input. The user can chose the logic functions MUX, AND, OR, NAND, NOR, inverter or noninverting buffer. All inputs can be connected to ground or Vcc as required. The device is designed for operation with a power supply range of 1.65V to 5.5V. The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using IOFF. The IOFF circuitry disables the output preventing damaging current backflow when the device is powered down. The user is reminded that the device can simulate several types of logic gates but may respond differently due to the Schmitt action at the inputs.

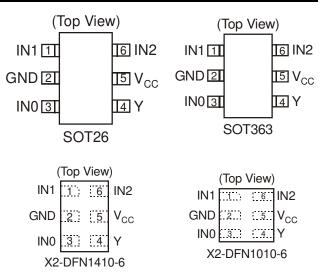
Features

- Wide Supply Voltage Range from 1.65V to 5.5V
- ± 24mA Output Drive at 3.3V
- CMOS low power consumption
- · IOFF Supports Partial-Power-Down Mode Operation
- Inputs accept up to 5.5V
- ESD Protection Exceeds JESD 22
 - 200-V Machine Model (A115-A)
 - 2000-V Human Body Model (A114-A)
- Latch-Up Exceeds 100mA per JESD 78, Class II
- Range of Package Options
- SOT26, SOT363, X2-DFN1410-6, and X2-DFN1010-6: Available
 - in "Green" Molding Compound (no Br, Sb)
 - Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
 - Halogen and Antimony Free. "Green" Device (Note 3)

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Pin Assignments



Applications

- Voltage Level Shifting
- General Purpose Logic
- Power Down Signal Isolation
- Wide array of products such as:
 - PCs, networking, notebooks, netbooks, PDAs
 - Computer peripherals, hard drives, CD/DVD ROM
 - TV, DVD, DVR, set top box
 - Cell Phones, Personal Navigation / GPS
 - MP3 players ,Cameras, Video Recorders

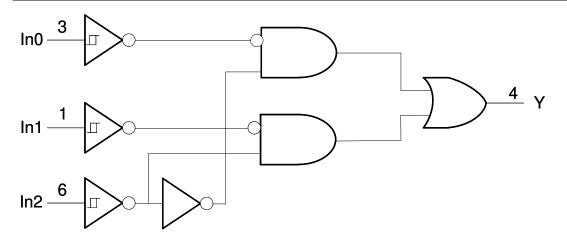


CONFIGURABLE MULTIPLE-FUNCTION GATE

Pin Descriptions

Pin Name	Description
IN1	Data Input
GND	Ground
IN0	Data Input
Y	Data Output
Vcc	Supply Voltage
IN2	Data Input

Logic Diagram

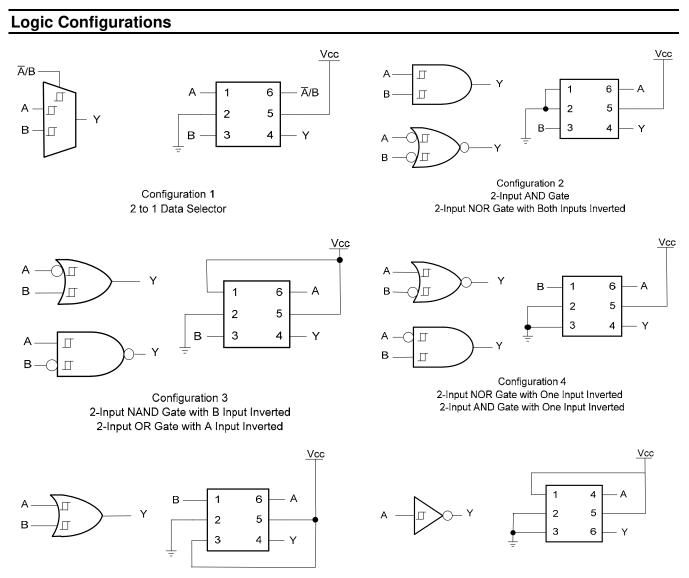


Function Table

	Inputs	Output	
IN2	IN1	IN0	Y
L	L	L	L
L	L	Н	L
L	н	L	н
L	н	Н	н
Н	L	L	L
Н	L	Н	Н
н	Н	L	L
Н	Н	Н	Н



CONFIGURABLE MULTIPLE-FUNCTION GATE



Configuration 6 Inverter

Configuration 5 2-Input OR Gate

Function Selection	Table
Logic Function	Configuration
2-to-1 Data Selector	1
2-input AND gate	2
2-input AND with inverted input	3, 4
2-input NOR with inverted input	3, 4
2-input OR	5
2-input NOR with both inputs inverted	2
1-input Inverter	6



CONFIGURABLE MULTIPLE-FUNCTION GATE

Absolute Maximum Ratings (Note 4)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to 6.5	V
VI	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage applied to output in high impedance or IOFF state	-0.5 to 6.5	V
Vo	Voltage applied to output in high or low state	-0.3 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current VI < 0	-50	mA
loк	Output Clamp Current	-50	mA
Io	Continuous output current	±50	mA
	Continuous current through Vdd or GND	±100	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Notes: 4. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

Recommended Operating Conditions (Note 5)

Symbol		Parameter	Min	Max	Unit
		Operating	1.65	5.5	V
Vcc	Operating Voltage	Data retention only	1.5		V
VI	Input Voltage		0	5.5	V
Vo	Output Voltage		0	V _{CC}	V
		V _{CC} = 1.65V		-4	
		$V_{CC} = 2.3V$		-8	
I _{OH}	High-level output current			-16	mA
		$V_{CC} = 3V$		-24	
		V _{CC} = 4.5V		-32	
		V _{CC} = 1.65V		4	
		V _{CC} = 2.3V		8	
IOL	Low-level output current			16	mA
		$V_{CC} = 3V$		24	
		$V_{CC} = 4.5V$		32	
		V _{CC} = 1.8V ± 0.15V, 2.5V ± 0.2V		20	
Δt/ΔV	Input transition rise or fall rate	V _{CC} = 3.3V ± 0.3V		10	ns/V
		$V_{CC} = 5V \pm 0.5V$		5	
TA	Operating free-air temperature		-40	+125	°C

Notes: 5. Unused inputs should be held at V_{CC} or Ground.



Electrical Characteristics $T_A = -40^{\circ}C$ to $+85^{\circ}C$ (All typical values are at $V_{CC} = 3.3V$, $T_A = +25^{\circ}C$)

Symbol	Parameter	Test Conditions	Vcc	Min	Тур	Max	Unit
			1.65V	0.70		1.20	
			2.3V	1.11		1.60	
V _{T+} Positive-going input threshold voltage	Positive-going input		3V	1.50		2.00	
	threshold voltage		4.5V	2.16		2.74	
			5.5V	2.61		3.33	
			1.65V	0.30		0.72	
			2.3V	0.58		1.00	
V _T -	Negative-going input		3V	0.80		1.30	
	threshold voltage		4.5V	1.21		1.95	
			5.5V	1.45		2.35	
			1.65V	0.30		0.62	
$\Delta V_{T} \qquad \begin{array}{c} Hysteresis \\ (V_{T+} - V_{T-}) \end{array}$		2.3V	0.40		0.80		
		3V	0.35		1.00		
		4.5V	0.55		1.10		
			5.5V	0.60		1.20	
		I _{OH} = -100μA	1.65V to 5.5V	V _{CC} -0.1			
		I _{OH} = -4mA	1.65V	1.2			
	High Level Output Voltage	I _{OH} = -8mA	2.3V	1.9			
V _{OH}		I _{OH} = -16mA		2.4			V
		I _{OH} = -24mA	3V	2.3			
		I _{OH} = -32mA	4.5V	3.8			
		I _{OL} = 100μA	1.65V to 5.5V			0.1	
		I _{OL} = 4mA	1.65V			0.45	
		I _{OL} = 8mA	2.3V			0.3	
V _{OL}	High-level Input Voltage	I _{OL} = 16mA				0.4	V
		I _{OL} = 24mA	3V			0.55	
		I _{OL} = 32mA	4.5V			0.55	
l _l	Input Current	$V_{I} = 5.5V \text{ or } GND$	0 to 5.5V			± 5	μA
I _{OFF}	Power Down Leakage Current	$V_{I} \text{ or } V_{O} = 5.5 V$	0			± 10	μA
I _{CC}	Supply Current	V _I = 5.5V of GND I _O =0	1.65V to 5.5V			10	μA
ΔI _{CC}	Additional Supply Current	One input at V_{CC} –0.6V Other inputs at V_{CC} or GND	3V to 5.5V			500	μA



Electrical Characteristics $T_A = -40^{\circ}C$ to $+125^{\circ}C$ (All typical values are at $V_{CC} = 3.3V$, $T_A = +25^{\circ}C$)

Symbol	Parameter	Test Conditions	Vcc	Min	Тур	Max	Unit
			1.65V	0.70		1.20	
			2.3V	1.11		1.60	
V- 0 0 1	Positive-going input		3V	1.50		2.00	
	threshold voltage		4.5V	2.16		2.74	
			5.5V	2.61		3.33	
			1.65V	0.30		0.75	
			2.3V	0.58		1.03	
V _{T-}	Negative-going input		3V	0.80		1.33	
	threshold voltage		4.5V	1.21		1.95	
			5.5V	1.45		2.35	
			1.65V	0.30		0.62	
			2.3V	0.37		0.80	
ΔV_T	$ \Delta V_T \qquad \begin{array}{l} \text{Hysteresis} \\ (V_{T+} - V_{T-}) \end{array} $		3V	0.32		1.00	
			4.5V	0.50		1.20	
			5.5V	0.55		1.40	
		I _{OH} = -100μA	1.65V to 5.5V	V _{CC} -0.1			
		I _{OH} = -4mA	1.65V	0.95			
		I _{OH} = -8mA	2.3V	1.7			1
V _{OH}	High Level Output Voltage	I _{OH} = -16mA	0 14	1.9			V
		I _{OH} = -24mA	3V	2.0			
		I _{OH} = -32mA	4.5V	3.4			
		I _{OL} = 100μA	1.65V to 5.5V			0.1	
		I _{OL} = 4mA	1.65V			0.7	
		I _{OL} = 8mA	2.3V			0.45	
V _{OL}	High-level Input Voltage	I _{OL} = 16mA				0.6	V
		I _{OL} = 24mA	3V			0.8	
		I _{OL} = 32mA	4.5V			0.8	
h	Input Current	V _I = 5.5V or GND	0 to 5.5V			± 100	μA
IOFF	Power Down Leakage Current	$V_{I} \text{ or } V_{O} = 5.5 V$	0			± 200	μA
I _{CC}	Supply Current	V _I = 5.5V of GND I _O =0	1.65V to 5.5V			200	μA
ΔI _{CC}	Additional Supply Current	One input at V_{CC} -0.6V Other inputs at V_{CC} or GND	3V to 5.5V			5000	μA



Electrical Characteristics (All typical values are at $V_{CC} = 3.3V$, $T_A = +25^{\circ}C$)

Symbol	Parameter	Test Conditions	Vcc	Min	Тур	Мах	Unit		
CI	Input Capacitance	$V_I = V_{CC} - or GND$	3.3		3.5		pF		
	θ _{IA} Thermal Resistance Junction-	SOT26			204				
		SOT363			371		0		
θ_{JA}		X2-DFN1410-6	(Note 6)		430		°C/W		
		X2-DFN1010-6			510				
		SOT26			52				
	Thermal Resistance Junction-	SOT363			143				
θ_{JC}	to-Case	X2-DFN1410-6	(Note 6)		190		°C/W		
		X2-DFN1010-6			250		1		

Notes: 6. Test condition for SOT26, SOT363, X2-DFN1410-6 and X2-DFN1010-6 : Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Switching Characteristics

Parameter	From	то		V _{CC} = 1.8V ± 0.15V		= 2.5V).2V	V _{CC} = 3.3V ± 0.3V			= 5V).5V	Unit	
	(Input)	(Input) (OUTPUT	(OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pd}	Any	Y	1.0	14.4	0.7	8.3	0.7	6.3	0.7	5.1	ns	

$T_A = -40^{\circ}C \text{ to } +125^{\circ}C$, $C_L = 30 \text{ or } 50pF$ as noted (see Figure 1)

Parameter	From	то	••	V _{CC} = 1.8V V _C ± 0.15V		: 2.5V).2V	V _{CC} = 3.3V ± 0.3V			= 5V).5V	Unit
	(Input)	(Input) (OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pd}	Any	Y	1.0	18.0	0.7	10.4	0.7	7.9	0.7	6.4	ns

Operating Characteristics

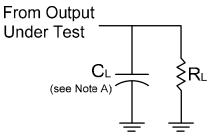
T_A = +25°C

	Parameter	Test Conditions	V _{CC} = 1.8V Typ.	V _{CC} = 2.5V Typ.	V _{CC} = 3.3V Typ.	V _{CC} = 5V Typ.	Unit
C _{pd}	Power dissipation capacitance	f = 10 MHz	22	22	23	24	pF

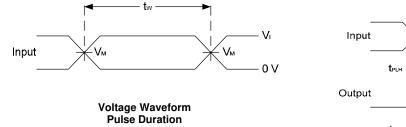


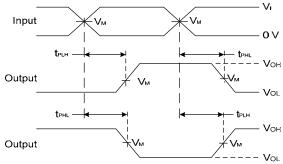
CONFIGURABLE MULTIPLE-FUNCTION GATE

Parameter Measurement Information



Vcc	Inputs		VM	CL	RL
	VI	t _r /t _f	• 101	UL	
1.8V±0.15V	V _{CC}	≤2ns	V _{CC} /2	30pF	1ΚΩ
2.5V±0.2V	V _{CC}	≤2ns	V _{CC} /2	30pF	500Ω
3.3V±0.3V	3V	≤2.5ns	1.5V	50pF	500Ω
5V±0.5V	V _{CC}	≤2.5ns	V _{CC} /2	50pF	500Ω





Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

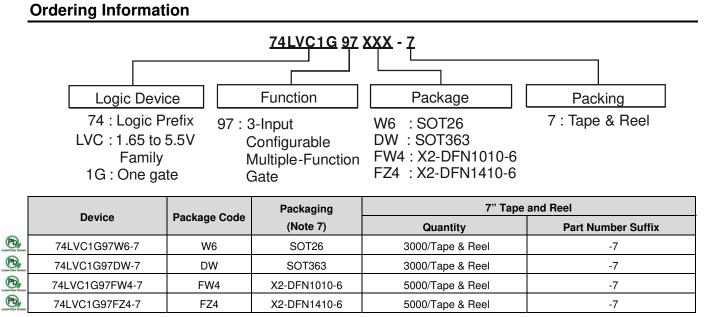
Figure 1. Load Circuit and Voltage Waveforms

Notes:

- A. Includes test lead and test apparatus capacitance.
- B. All pulses are supplied at pulse repetition rate \leq 10 MHz
- C. Inputs are measured separately one transition per measurement
- D. t_{PLH} and t_{PHL} are the same as t_{PD}



CONFIGURABLE MULTIPLE-FUNCTION GATE



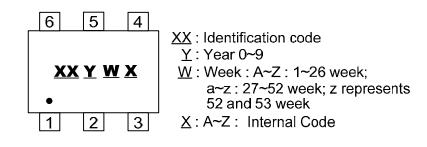
Notes: 7. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



CONFIGURABLE MULTIPLE-FUNCTION GATE

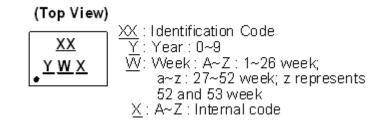
Marking Information

(1) SOT26, SOT363



Part Number	Package	Identification Code
74LVC1G97W6	SOT26	TY
74LVC1G97DW	SOT363	TY

(2) X2-DFN1010-6, X2-DFN1410-6



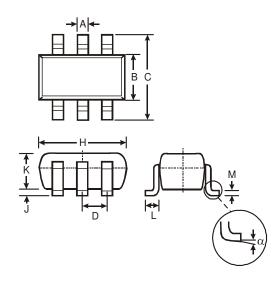
Part Number	Package	Identification Code
74LVC1G97FW4	X2-DFN1010-6	TY
74LVC1G97FZ4	X2-DFN1410-6	TY



CONFIGURABLE MULTIPLE-FUNCTION GATE

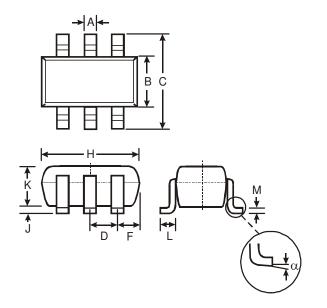
Package Outline Dimensions (All Dimensions in mm)

(1) SOT26



SOT26				
Dim	Min	Max	Тур	
Α	0.35	0.50	0.38	
в	1.50	1.70	1.60	
c	2.70	3.00	2.80	
D		—	0.95	
н	2.90	3.10	3.00	
J	0.013	0.10	0.05	
к	1.00	1.30	1.10	
1	0.35	0.55	0.40	
М	0.10	0.20	0.15	
ರ	0°	8°		
All Dimensions in mm				

(2) SOT363



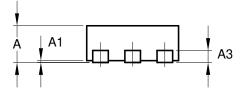
	SOT363			
Dim	Min	Max		
Α	0.10	0.30		
В	1.15	1.35		
С	2.00	2.20		
D	0.65	Тур		
F	0.40	0.45		
н	1.80	2.20		
J	0	0.10		
К	0.90	1.00		
L	0.25	0.40		
М	0.10	0.22		
α	0°	8°		
All Dimensions in mm				

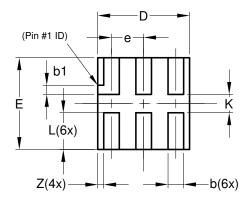


CONFIGURABLE MULTIPLE-FUNCTION GATE

Package Outline Dimensions (All Dimensions in mm)

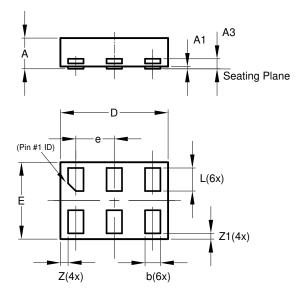
(3) X2-DFN1010-6





	X2-DFN1010-6				
Dim	Min	Max	Тур		
Α	—	0.40	0.39		
A1	0.00	0.05	0.02		
A3			0.13		
Ь	0.14	0.20	0.17		
b1	0.05	0.15	0.10		
D	0.95	1.05	1.00		
ш	0.95	1.05	1.00		
e			0.35		
1	0.35	0.45	0.40		
К	0.15	_			
Z			0.065		
All	All Dimensions in mm				

(4) X2-DFN1410-6



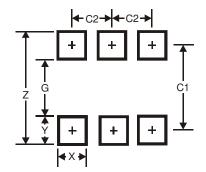
X2-DFN1410-6				
Dim	Dim Min Max Typ			
Α	_	0.40	0.39	
A1	0.00	0.05	0.02	
A3		_	0.13	
b	0.15	0.25	0.20	
D	1.35	1.45	1.40	
ш	0.95	1.05	1.00	
е		_	0.50	
L	0.25	0.35	0.30	
Z			0.10	
Z1	0.045	0.105	0.075	
All Dimensions in mm				



CONFIGURABLE MULTIPLE-FUNCTION GATE

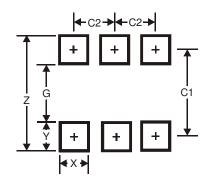
Suggest Pad Layout

(1) SOT26



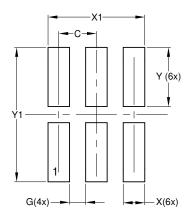
Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95

(2) SOT363



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Y	0.6
C1	1.9
C2	0.65

(3) X2-DFN1010-6



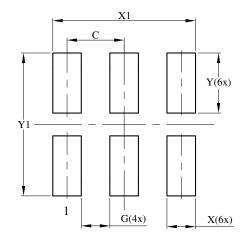
Dimensions	Value (in mm)
С	0.350
G	0.150
Х	0.200
X1	0.900
Y	0.550
Y1	1.250



CONFIGURABLE MULTIPLE-FUNCTION GATE

Suggest Pad Layout

(4) X2-DFN1410-6



Dimensions	Value (in mm)
С	0.500
G	0.250
Х	0.250
X1	1.250
Y	0.525
Y1	1.250



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